

isc Silicon PNP Power Transistor

2SA2223

DESCRIPTION

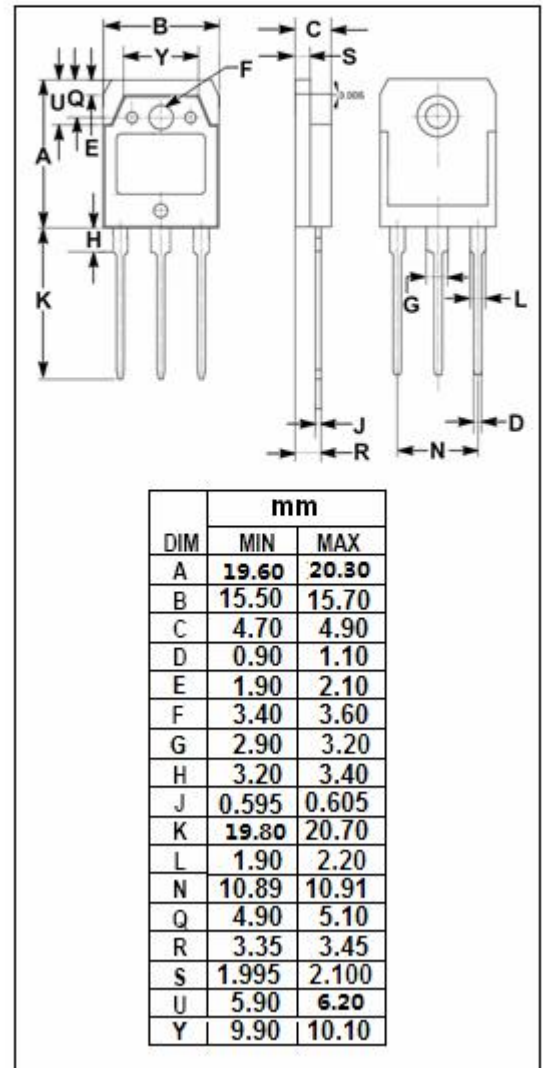
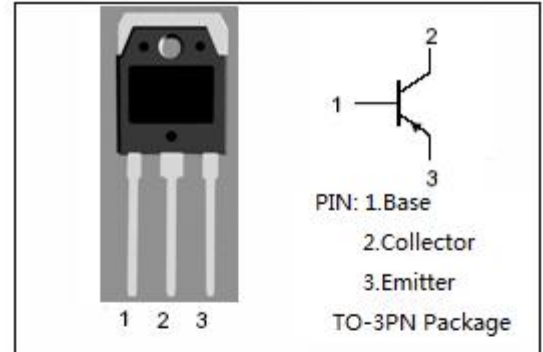
- High frequency multi emitter transistor
- Small package(TO-3P)
- High power handling capacity ,160W
- Complement to Type 2SC6145
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.

APPLICATIONS

- Signal transistors for audio amplifiers
- Audio market

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-230	V
V _{CEO}	Collector-Emitter Voltage	-230	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current-Continuous	-15	A
I _B	Base Current-Continuous	-4.0	A
P _C	Collector Power Dissipation @ T _C =25°C	160	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon PNP Power Transistor**2SA2223****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -25\text{mA}; I_B = 0$	-230			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -0.5\text{A}$			-0.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -230\text{V}; I_E = 0$			-10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-10	μA
h_{FE}	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -4\text{V}$	40		140	
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1.0\text{MHz}$		500		pF
f_T	Current-Gain—Bandwidth Product	$I_C = -2\text{A}; V_{CE} = -12\text{V}$		35		MHz

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◆ **h_{FE} Classifications**

R	O	Y
40-80	50-100	70-140